

# **FJPF5200 NPN Epitaxial Silicon Transistor**

# Applications

- · High-Fidelity Audio Output Amplifier
- General Purpose Power Amplifier •

## **Features**

- High Current Capability: I<sub>C</sub> = 17A.
- High Power Dissipation : 50watts. •
- High Frequency : 30MHz. •
- High Voltage : V<sub>CEO</sub>=250V
- Wide S.O.A for reliable operation.
- Excellent Gain Linearity for low THD.
- Complement to FJPF1943
- Thermal and electrical Spice models are available.
- Same transistor is also available in:
  - -- TO264 package, 2SC5200/FJL4315 : 150 watts
  - -- TO3P package, 2SC5242/FJA4313 : 130 watts
  - -- TO220 package, FJP5200 : 80 watts

# TO-220F 1.Base 2.Collector 3.Emitter

| Absolute Maximum Ratings' | K<br>T <sub>a</sub> = 25°C unless otherwise noted |
|---------------------------|---|
|---------------------------|---|

| Symbol                            | Parameter   | Ratings     | Units     |  |
|-----------------------------------|---|-------------|-----------|--|
| BV <sub>CBO</sub>                 | Collector-Base Voltage  | 250         | V         |  |
| BV <sub>CEO</sub>                 | Collector-Emitter Voltage   | 250 V       |           |  |
| BV <sub>EBO</sub>                 | Emitter-Base Voltage  | 5           | V         |  |
| I <sub>C</sub>                    | Collector Current(DC)   | 17          | А         |  |
| I <sub>B</sub>                    | Base Current  | 1.5         | А         |  |
| P <sub>D</sub>                    | Total Device Dissipation(T <sub>C</sub> =25°C)<br>Derate above 25°C | 50<br>0.4   | W<br>W/°C |  |
| T <sub>J</sub> , T <sub>STG</sub> | Junction and Storage Temperature                                    | - 50 ~ +150 | °C        |  |

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

## Thermal Characteristics\* T<sub>a</sub>=25°C unless otherwise noted

| Symbol              | Parameter                            | Max. | Units |
|---------------------|--------------------------------------|------|-------|
| $R_{	ext{	heta}JC}$ | Thermal Resistance, Junction to Case | 2.5  | °C/W  |

\* Device mounted on minimum pad size

## h<sub>FE</sub> Classification

| Classification   | R        | 0        |
|------------------|----------|----------|
| h <sub>FE1</sub> | 55 ~ 110 | 80 ~ 160 |



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| Symbol                | Parameter                            | Test Condition                           | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|--|------|------|------|-------|
| BV <sub>CBO</sub>     | Collector-Base Breakdown Voltage     | I <sub>C</sub> =5mA, I <sub>E</sub> =0   | 250  |      |      | V     |
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> =10mA, R <sub>BE</sub> =∞ | 250  |      |      | V     |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage       | I <sub>E</sub> =5mA, I <sub>C</sub> =0   | 5    |      |      | V     |
| I <sub>CBO</sub>      | Collector Cut-off Current            | V <sub>CB</sub> =230V, I <sub>E</sub> =0 |      |      | 5.0  | μΑ    |
| I <sub>EBO</sub>      | Emitter Cut-off Current              | V <sub>EB</sub> =5V, I <sub>C</sub> =0   |      |      | 5.0  | μΑ    |
| h <sub>FE1</sub>      | DC Current Gain                      | V <sub>CE</sub> =5V, I <sub>C</sub> =1A  | 55   |      | 160  |       |
| h <sub>FE2</sub>      | DC Current Gain                      | V <sub>CE</sub> =5V, I <sub>C</sub> =7A  | 35   | 60   |      |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> =8A, I <sub>B</sub> =0.8A |      | 0.4  | 3.0  | V     |
| V <sub>BE</sub> (on)  | Base-Emitter On Voltage              | V <sub>CE</sub> =5V, I <sub>C</sub> =7A  |      | 1.0  | 1.5  | V     |
| f <sub>T</sub>        | Current Gain Bandwidth Product       | V <sub>CE</sub> =5V, I <sub>C</sub> =1A  |      | 30   |      | MHz   |
| C <sub>ob</sub>       | Output Capacitance                   | V <sub>CB</sub> =10V, f=1MHz             |      | 200  |      | pF    |

## Electrical Characteristics\* Ta=25°C unless otherwise noted

\* Pulse Test: Pulse Widt=20  $\mu s,$  Duty Cycle≤2%

# **Ordering Information**

| Part Number | Marking | Package | Packing Method | Remarks      |
|-------------|---------|---------|----------------|--------------|
| FJPF5200RTU | J5200R  | TO-220F | TUBE           | hFE1 R grade |
| FJPF5200OTU | J5200O  | TO-220F | TUBE           | hFE1 O grade |

# **Typical Characteristics**



Figure 1. Static Characteristic



Figure 3. DC current Gain ( O grade )







Figure 2. DC current Gain ( R grade )



Figure 4. Collector-Emitter Saturation Voltage







Figure 7. Thermal Resistance

Figure 8. Power Derating

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